Octal 3-State Non-Inverting Transparent Latch

High-Performance Silicon-Gate CMOS

The 74HC373 is identical in pinout to the LS373. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

These latches appear transparent to data (i.e., the outputs change asynchronously) when Latch Enable is high. When Latch Enable goes low, data meeting the setup and hold time becomes latched.

The Output Enable input does not affect the state of the latches, but when Output Enable is high, all device outputs are forced to the high-impedance state. Thus, data may be latched even when the outputs are not enabled.

The HC373A is identical in function to the HC573A which has the data inputs on the opposite side of the package from the outputs to facilitate PC board layout.

The HC373A is the non-inverting version of the HC533A.

Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the JEDEC Standard No. 7.0 A Requirements
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 186 FETs or 46.5 Equivalent Gates
- This is a Pb-Free Device



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		DIAGRAM
20 1	TSSOP-20 DT SUFFIX CASE 948E	20 AAAAAAAAAAA HC 373 ALYW • O • 1 00000000000000000000000000000000000
HC373	= Specific D	evice Code
A	= Assembly	Location
L	= Wafer Lot	

= Year

Υ

- W = Work Week
 - = Pb-Free Package

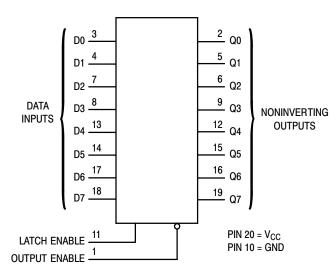
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

1

LOGIC DIAGRAM



PIN ASSIGNMENT

	1•	20	∃ v _{cc}
Q0 [2	19] Q7
D0 [3	18] D7
D1 [4	17] D6
Q1 [5	16] Q6
Q2 [6	15] Q5
D2 [7	14] D5
D3 [8	13] D4
Q3 [9	12] Q4
GND [10	11	LATCH ENABLE

FUNCTION TABLE

	Inputs				
Output Enable	Latch Enable	D	q		
L	Н	Н	Н		
L	н	L	L		
L	L	Х	No Change		
Ιн	Х	Х	Z		

X = Don't Care

Z = High Impedance

Design Criteria	Value	Units
Internal Gate Count*	46.5	ea
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μW
Speed Power Product	0.0075	рJ

*Equivalent to a two-input NAND gate.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to V_{CC} + 0.5	V
Vout	DC Output Voltage (Referenced to GND)	-0.5 to V_{CC} + 0.5	V
l _{in}	DC Input Current, per Pin	±20	mA
l _{out}	DC Output Current, per Pin	±35	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±75	mA
PD	Power Dissipation in Still Air, TSSOP Package†	450	mW
T _{stg}	Storage Temperature	– 65 to + 150	°C
ΤL	Lead Temperature, 1 mm from Case for 10 Seconds (TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric ields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the ange GND \leq (V_{in} or V_{out}) \leq V_{CC}. Unused inputs must always be

ied to an appropriate logic voltage evel (e.g., either GND or V_{CC}). Jnused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Parameter			
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V	
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Reference	OC Input Voltage, Output Voltage (Referenced to GND)		V _{CC}	V
T _A	Operating Temperature, All Package Type	Operating Temperature, All Package Types			°C
t _r , t _f	(Figure 1) V	_{CC} = 2.0 V _{CC} = 4.5 V _{CC} = 6.0 V	0 0 0	1000 500 400	ns

ORDERING INFORMATION

Device	Package	Shipping [†]
74HC373DTR2G	TSSOP-20*	2500 Units / Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*This package is inherently Pb-Free.

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V _{CC} (V)	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
VIH	Minimum High-Level Input	$V_{out} = V_{CC} - 0.1 V$	2.0	1.5	1.5	1.5	V
	Voltage	$ I_{out} \le 20 \mu A$	3.0	2.1	2.1	2.1	
	_		4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
VIL	Maximum Low-Level Input	$V_{out} = 0.1 V$	2.0	0.5	0.5	0.5	V
	Voltage	l _{out} ≤ 20 μA	3.0	0.9	0.9	0.9	
	_		4.5	1.35	1.35	1.35	
			6.0	1.8	1.8	1.8	
V _{OH}	Minimum High-Level Output	V _{in} = V _{IH}	2.0	1.9	1.9	1.9	V
	Voltage	l _{out} ≤ 20 μA	4.5	4.4	4.4	4.4	
			6.0	5.9	5.9	5.9	
		$V_{in} = V_{IH}$ $ I_{out} \le 2.4 \text{ mA}$	3.0	2.48	2.34	2.2	
		$ I_{out} \le 6.0 \text{ mA}$	4.5	3.98	3.84	3.7	
		$ I_{out} \le 7.8 \text{ mA}$	6.0	5.48	5.34	5.2	
V _{OL}	Maximum Low-Level Output	$V_{in} = V_{IL}$	2.0	0.1	0.1	0.1	V
02	Voltage	l _{out} ≤ 20 μA	4.5	0.1	0.1	0.1	
	_		6.0	0.1	0.1	0.1	
		$V_{in} = V_{IL}$ $ I_{out} \le 2.4 \text{ mA}$	3.0	0.26	0.33	0.4	
		$ I_{out} \le 6.0 \text{ mA}$	4.5	0.26	0.33	0.4	
		$ I_{out} \le 7.8 \text{ mA}$	6.0	0.26	0.33	0.4	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	±0.1	±1.0	±1.0	μA
I _{OZ}	Maximum Three-State	Output in High-Impedance State	6.0	±0.5	±5.0	±10	μA
	Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$					
		$V_{out} = V_{CC}$ or GND					
I _{CC}	Maximum Quiescent Supply	V _{in} = V _{CC} or GND	6.0	4.0	40	40	μA
	Current (per Package)	I _{out} = 0 μA					

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		V _{CC}	Guaranteed Limit			
Symbol	Parameter	Ň	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
t _{PLH}	Maximum Propagation Delay, Input D to Q	2.0	125	155	190	ns
t _{PHL}	(Figures 1 and 5)	3.0	80	110	130	
		4.5	25	31	38	
		6.0	21	26	32	
t _{PLH}	Maximum Propagation Delay, Latch Enable to Q	2.0	140	175	210	ns
t _{PHL}	(Figures 2 and 5)	3.0	90	120	140	
		4.5	28	35	42	
		6.0	24	30	36	
t _{PLZ}	Maximum Propagation Delay, Output Enable to Q	2.0	150	190	225	ns
t _{PHZ}	(Figures 3 and 6)	3.0	100	125	150	
		4.5	30	38	45	
		6.0	26	33	38	
t _{PZL}	Maximum Propagation Delay, Output Enable to Q	2.0	150	190	225	ns
t _{PZH}	(Figures 3 and 6)	3.0	100	125	150	
		4.5	30	38	45	
		6.0	26	33	38	
t _{TLH}	Maximum Output Transition Time, Any Output	2.0	60	75	90	ns
t _{THL}	(Figures 1 and 5)	3.0	23	27	32	
		4.5	12	15	18	
		6.0	10	13	15	
C _{in}	Maximum Input Capacitance		10	10	10	pF
C _{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State)		15	15	15	pF

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6.0 \text{ ns}$)

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Per Enabled Output)*	36	рF

* Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

				Guaranteed Limit						
			v _{cc}	– 55 to	o 25°C	≤ 8	5°C	≤ 12	25°C	
Symbol	Parameter	Figure	(V)	Min	Max	Min	Max	Min	Max	Unit
t _{su}	Minimum Setup Time, Input D to Latch Enable	4	2.0 3.0 4.5 6.0	25 20 5.0 5.0		30 25 6.0 6.0		40 30 8.0 7.0		ns
t _h	Minimum Hold Time, Latch Enable to Input D	4	2.0 3.0 4.5 6.0	5.0 5.0 5.0 5.0		5.0 5.0 5 0 5.0		5.0 5.0 5.0 5.0		ns
t _w	Minimum Pulse Width, Latch Enable	2	2.0 3.0 4.5 6.0	60 23 12 10		75 27 15 13		90 32 18 15		ns
t _r , t _f	Maximum Input Rise and Fall Times	1	2.0 3.0 4.5 6.0		1000 800 500 400		1000 800 500 400		1000 800 500 400	ns

TIMING REQUIREMENTS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6.0 \text{ ns}$)

SWITCHING WAVEFORMS

LATCH ENABLE

Q

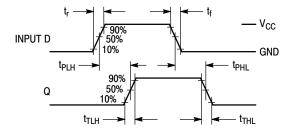
50%

t_{PLH}

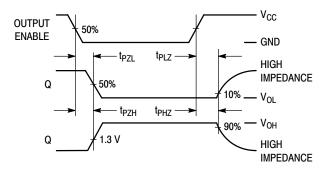
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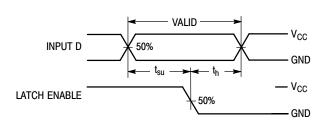
t_{PHL}

Figure 2.









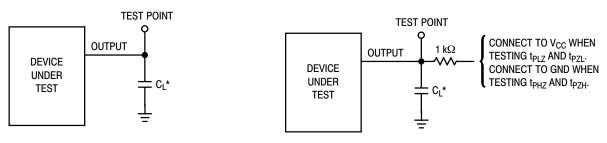
 V_{CC}

GND

Figure 3.



TEST CIRCUITS



*Includes all probe and jig capacitance



*Includes all probe and jig capacitance



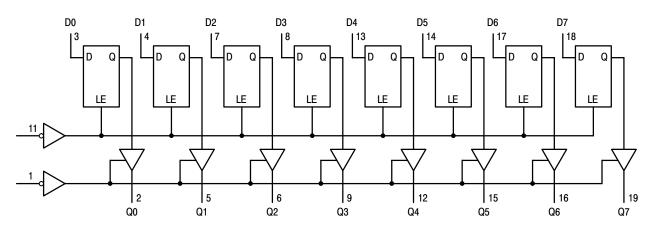
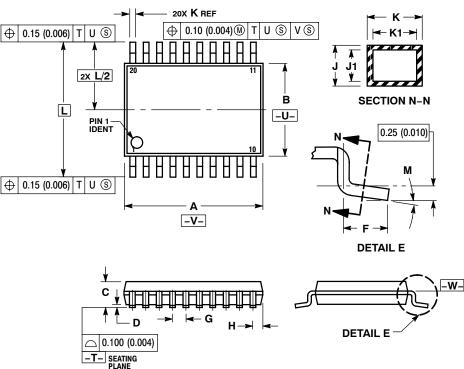


Figure 7. EXPANDED LOGIC DIAGRAM

PACKAGE DIMENSIONS

TSSOP-20 CASE 948E-02 **ISSUE C**



NOTES:

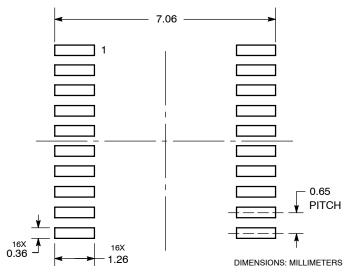
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
CONTROLLING DIMENSION: MILLIMETER.
DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION.
INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION, ALLOWABLE DAMBAR PROTRUSION, ALLOWABLE DAMBAR PROTRUSION, SHALL BE 0.08

(0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL

DIMENSION AI MAXIMUM MAI EHIAL CONDITION. 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026	BSC
Η	0.27	0.37	0.011	0.015
ſ	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
Κ	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L		6.40 BSC		BSC
Μ	0°	8°	0°	8°

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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